

**METHOD FOR INTERCONNECTION BETWEEN TRANSFER DEVICES
AND STORAGE CAPACITORS IN MEMORY CELLS AND DEVICE
FORMED THEREBY**

105,739

ABSTRACT OF THE DISCLOSURE

5 The preferred embodiment of the present invention provides unique structure
for connecting between a storage capacitor and a transfer device in a memory cell and
a method for fabricating the same. The preferred embodiment of the present
invention forms a capacitor structure having a "lip" at its top on the side the
connection is to be made. To form the connection, dopant is diffused from the lower
10 surface of the capacitor step and into the substrate, forming a surface strap to connect
between the storage capacitor and the transfer device. This surface strap has the
advantage of being self aligned with the storage capacitor and the transfer device,
facilitating higher memory cell densities. The present invention can be used to form
connections between storage capacitors and memory cells in a wide variety of
15 devices.